

RJK2017DPP

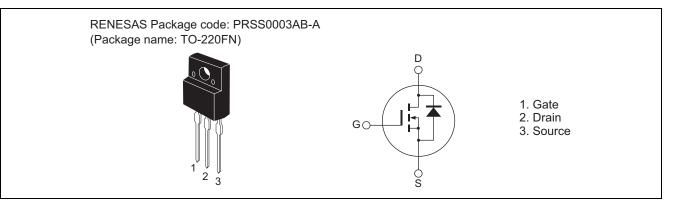
Silicon N Channel MOS FET High Speed Power Switching

> REJ03G1797-0200 Rev.2.00 Aug 26, 2009

Features

- Low on-resistance
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D Note4	45	Α
Drain peak current	Note1	135	А
Body-drain diode reverse drain current	I _{DR}	45	А
Avalanche current	I _{AP} Note3	12	А
Avalanche energy	E _{AR} ^{Note3}	9.6	mJ
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tc = 25°C

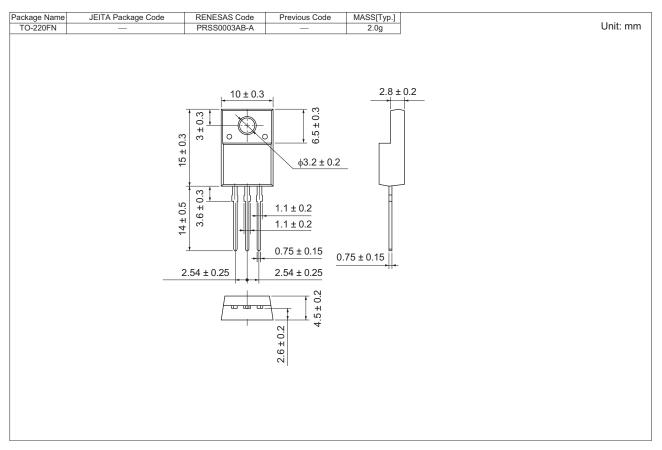
- 3. STch = 25°C, Tch \leq 150°C
- 4. Limited by maximum safe operation area

Electrical Characteristics

						$(Ta = 25^{\circ}C)$
Item	Symbol	Min	Тур	Max	Unit	Test conditions
Drain to source breakdown voltage	V _{(BR)DSS}	200	—	—	V	I _D = 10 mA, V _{GS} = 0
Zero gate voltage drain current	I _{DSS}		—	1	μΑ	V_{DS} = 200 V, V_{GS} = 0
Gate to source leak current	I _{GSS}		_	±1	μΑ	V_{GS} = ±30 V, V_{DS} = 0
Gate to source cutoff voltage	V _{GS(off)}	2	_	4	V	V _{DS} = 10 V, I _D = 1 mA
Static drain to source on state resistance	R _{DS(on)}		0.036	0.047	Ω	I_D = 22.5 A, V_{GS} = 10 V ^{Note5}
Input capacitance	Ciss	_	4800	_	pF	V _{DS} = 25 V V _{GS} = 0 f = 1 MHz
Output capacitance	Coss	_	290	_	pF	
Reverse transfer capacitance	Crss		90	—	рF	
Turn-on delay time	t _{d(on)}	_	50	—	ns	$I_{D} = 22.5 \text{ A} V_{GS} = 10 \text{ V} R_{L} = 4.5 \Omega Rg = 10 \Omega$
Rise time	tr	—	40	—	ns	
Turn-off delay time	t _{d(off)}	—	95	—	ns	
Fall time	t _f		40	—	ns	
Total gate charge	Qg		66	—	nC	V _{DD} = 160 V V _{GS} = 10 V I _D = 45 A
Gate to source charge	Qgs	—	26	—	nC	
Gate to drain charge	Qgd	_	16	_	nC	
Body-drain diode forward voltage	V _{DF}	_	0.88	1.35	V	$I_F = 45 \text{ A}, V_{GS} = 0^{\text{Note5}}$
Body-drain diode reverse recovery time	t _{rr}		150		ns	$I_F = 45 \text{ A}, V_{GS} = 0$ $di_F/dt = 100 \text{ A}/\mu\text{s}$

Notes: 5. Pulse test

Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK2017DPP-00-T2	1050 pcs	Box (Tube)

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